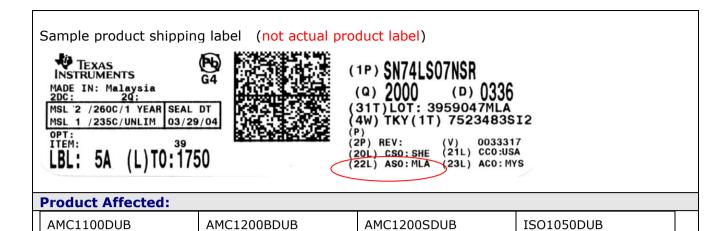
DCI	M. MI		201005	1 4000					_	DCN D		M 15 2010	
	Numbe		201905			(DAL A.)				PCN D		May 15 2019	
Titl							s an alternat		_		r Sele	ct Devices	
Cus	stomer C	ontac	t:   <u>PCI</u>	Mana	<u>ger</u>	<b>Dept</b> :		lity Serv			D-1-		
<b>Proposed 1<sup>st</sup> Ship Date:</b> Aug 1					g 15 2				ated Sample Availability:			Date provided at sample request	
Cha	Change Type:												
Assembly Site						☐ Design ☐				Wafer Bump Site			
	Assemb					☐ Data Sheet ☐					Wafer Bump Material		
X	Assembly Materials				_   _	Part number change					Wafer Bump Process		
Mechanical Specification					Test Site				Wafer Fab Site				
Packing/Shipping/Labeling					Test Process			${\color{red} oxed{H}}$	Wafer Fab Materials Wafer Fab Process				
						PCN Details					Process		
Doc	cription	of Ch	angol			PCI	1 Details						
	scription			ed to	annoi	unce th	e qualificatio	n of TI M	lala	vsia (N	/I Δ ) =	s an Additional	
							elow. Curren						
	erences a			i ucvi	CC3 31	iowii be	now. Curren	c asserin	Лу	Sites a	na ma	Certai	
		• •• .											
					-								
						Hana				<b>1alays</b>			
			nt Com			SID#400154				211470			
		Molo	compo	und		SID	#450522		4221499				
Rea	son for	Chan	ie:										
	Continuity of Supply												
					F:4 F		n Ovelity e	. Daliak	:::4.		ikiya	/ negative):	
		Шра	Ct on F	orm,	ril, F	unctio	n, Quanty o	гкенар	IIIL	y (pos	itive	/ negative):	
Non	ie icipated	limna	ct on M	latori	al Do	clarati	on						
AIII	No Imp						clarations or	Product (	^on	tent re	norts	are driven	
	Materia												
				from production data and will be available following the production release. Upon production release the revised									
				reports can be obtained at the site link below									
<u>  ht</u>			http:	http://www.ti.com/quality/docs/materialcontentsearch.tsp									
Cha			! . !	. L   C	***		f th:	- DCN-					
Clia	Changes to product identification resulting from this PCN:												
Assembly Site Assembly Site Original			Origin	gin (22L) Assembly Country Code (2				LL)	.) Assembly City				
Hana		HNA				Т	НА			P	Ayutthaya		
TI Malaysia		sia	MLA			MY		YS	S		Kua	ıla Lumpur	





AMC1100DUBR

TI Information Selective Disclosure

ISO1050DUBR

## Qualification Results Data Displayed as: Number of lots / Total sample size / Total failed

AMC1200SDUBR

Type	Test Name / Condition	Duration	Qual Device: . <u>ISO1050DUB</u>
AC	Autoclave 121C	96 Hours	3/231/0
CDM	ESD - CDM	1500 V	3/9/0
ED	Electrical Characterization	Per Datasheet Parameters	Pass
HAST	Biased HAST, 130C/85%RH	96 Hours	3/231/0
HTOL	Life Test, 125C	1000 Hours	3/150/0
HTSL	High Temp Storage Bake 170C	420 Hours	3/231/0
LI	Lead Pull to Destruction	Leads	1/24/0
SBS	Ball Shear	Wires	3/228/0
TC	Temperature Cycle, -65/150C	500 Cycles	3/231/0
WBP	Bond Pull	Wires	3/228/0

- QBS: Qual By Similarity
- Qual Device ISO1050DUB is qualified at LEVEL4-260C
- Device ISO1050DUB contains multiple dies.
- Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable
- The following are equivalent HTOL options based on an activation energy of 0.7eV: 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours
- The following are equivalent HTSL options based on an activation energy of 0.7eV : 150C/1k Hours, and 170C/420 Hours
- $The following are equivalent Temp Cycle options per JESD47: -55C/125C/700 \ Cycles \ and \ -65C/150C/500 \ Cycles$

AMC1200BDUBR

Quality and Environmental data is available at TI's external Web site: http://www.ti.com/

## Green/Pb-free Status:

Qualified Pb-Free(SMT) and Green

For questions regarding this notice, e-mails can be sent to the contacts shown below or your local Field Sales Representative.

Location	E-Mail
USA	PCNAmericasContact@list.ti.com
Europe	PCNEuropeContact@list.ti.com
Asia Pacific	PCNAsiaContact@list.ti.com
WW PCN Team	PCN www admin_team@list.ti.com